





SIL for improved sensitivity and spatial resolution

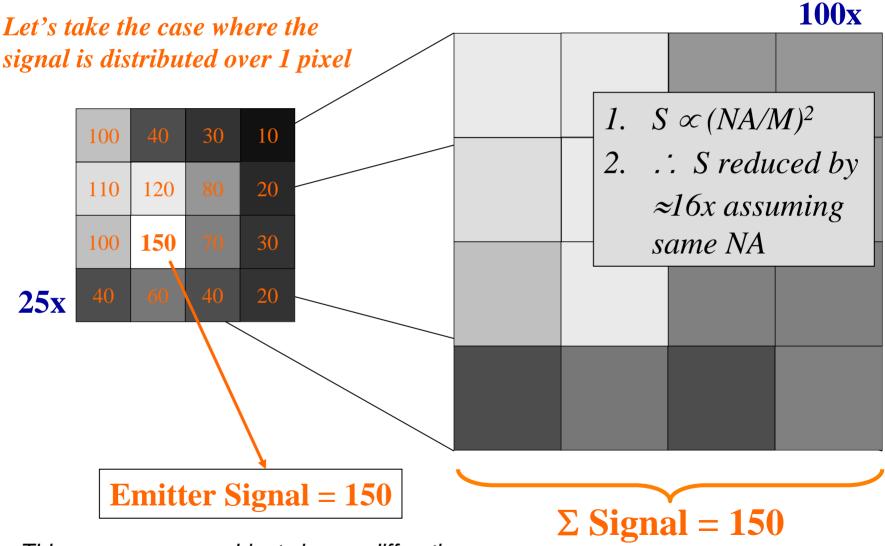
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EUFANET - Jan 26 2009

Why is Sensitivity important?

- High resolution fault localization requires *enough* sensitivity at high magnification
- High Sensitivity is required to obtain/maintain "fault detectibility" for advanced technology nodes because Vdd keeps decreasing
- High Sensitivity is required for new dynamic applications

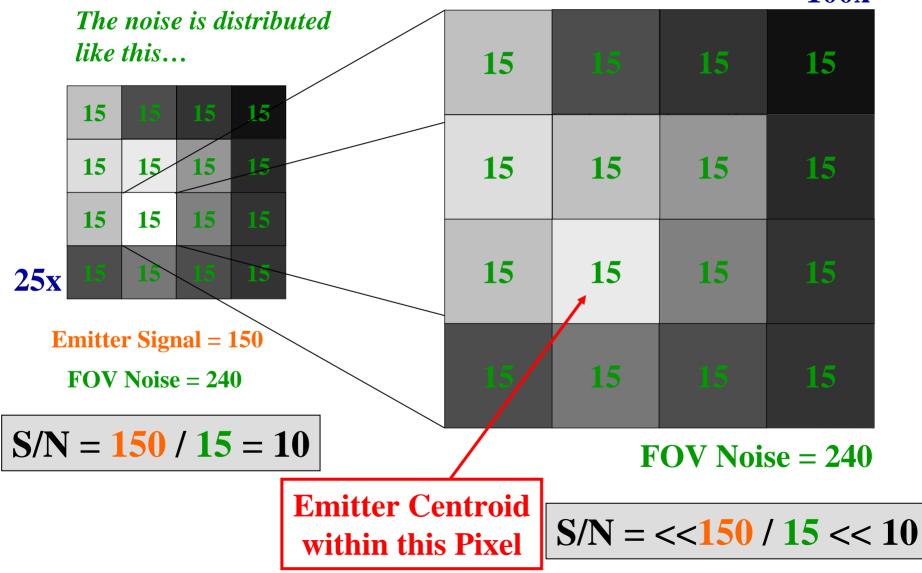
Example: Magnification and SNR (1)



This case assumes object size >> diffractionlimited spot size

Example: Magnification and SNR (2)

100x

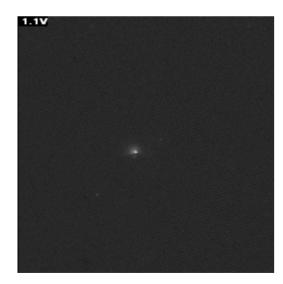


Is high magnification so beneficial ?

Lens	NA	Mag	(NA/Mag)2	relative
1x	0.25	1	6.3E-02	100.00
20x	0.5	20	6.3E-04	1.00
50x	0.6	50	1.4E-04	0.23
Mit 100x HR	0.7	100	4.9E-05	0.08
LWD SIL	1.45	175	6.9E-05	0.11
STD SIL	2.45	220	1.2E-04	0.20

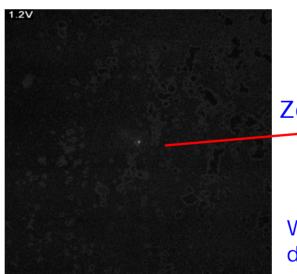
This case assumes object size >> diffraction-limited spot size

May be not for sensitivity but certainly for resolution

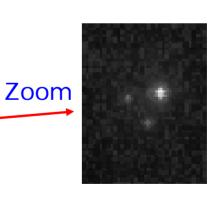


20x – 256 camera

Images courtesy of ST

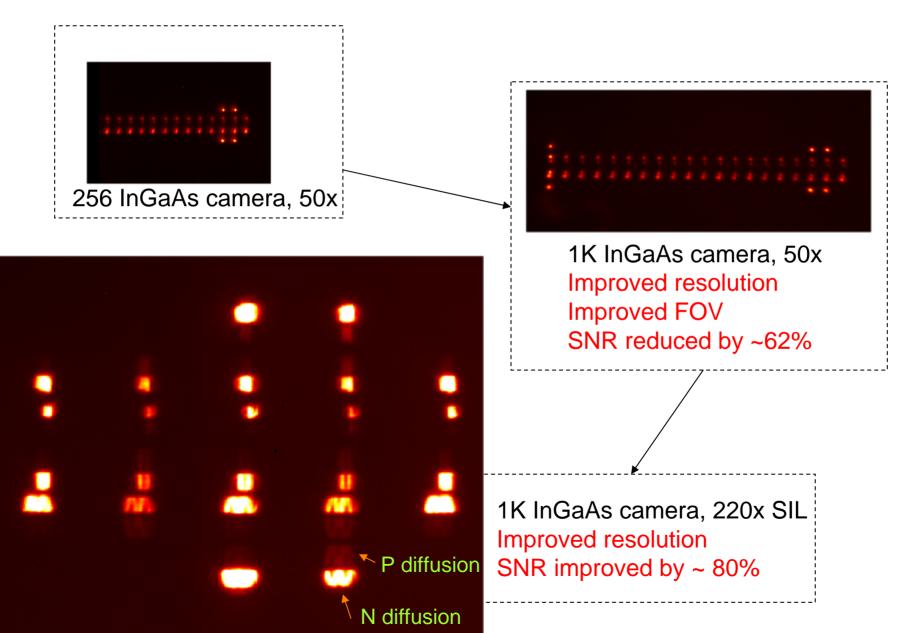


20x – 1K camera

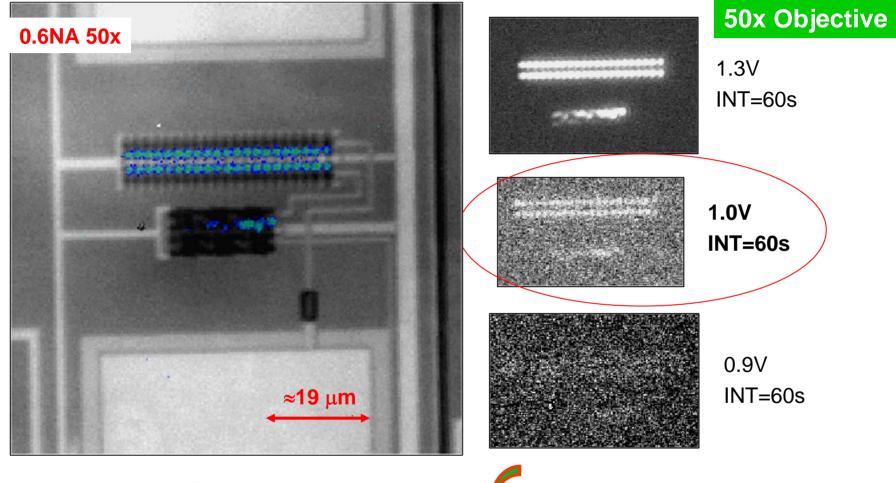


When the image is displayed in its full resolution, we clearly see 3 spots with 20x which is not the case with the 256 camera

Improved SNR with SIL – Azuma 0.18um



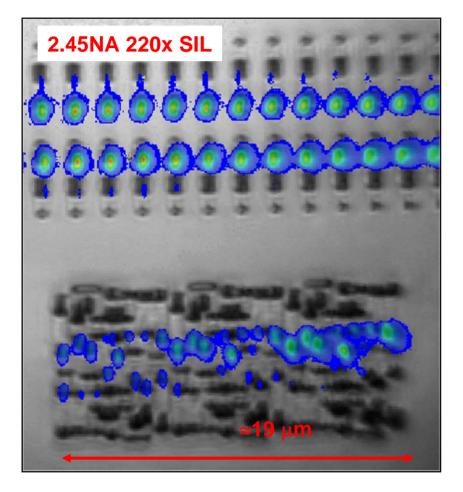
1Kx1K InGaAs Sensitivity Comparison (1/2)



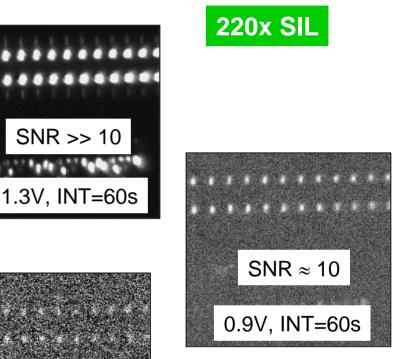
50x, 0.6NA 1K InGaAs overlay image (cropped) of 140nm ring oscillator. 1.3V, INT = 60s. 100 μ m substrate thickness.

Sensitivity limit at 50x in 60s = 1.0V

1Kx1K InGaAs Sensitivity Comparison (2/2)



220x SIL (2.45NA) 1K InGaAs overlay image (cropped) of 140nm ring oscillator. 1.3V, INT = 60s. 100 μ m substrate thickness.



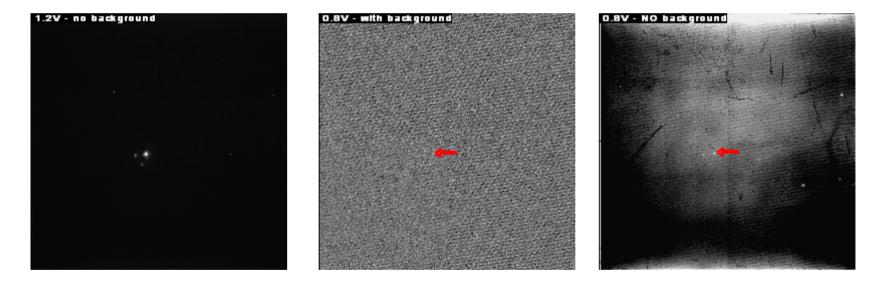
Sensitivity limit with SIL in 60s: 800mV (200mV better than 50x)

 $SNR \approx 5$

0.8V, INT=60s

Sensitivity limit for each lens (1/3)

- Core Voltage is changed by 100mV steps
- Integration time is constant for each acquisition
- Device is about 100µm Si thick



50x - 1.2V

Images courtesy of ST

Detection limit $\approx 0.8V$ No background subtraction provides better SNR but is less uniform

Sensitivity limit for each lens (2/3)

STD SIL images

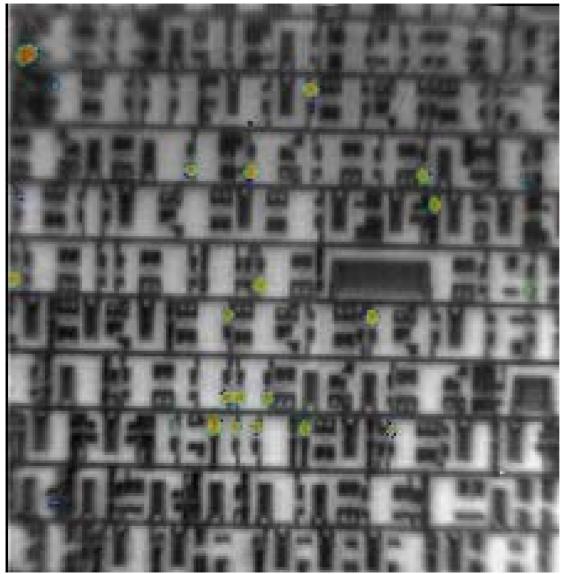


Images courtesy of ST

	LN2 InGaAs
1x	0.9V
20x	0.9V
50x	0.9V
Mit 100x HR	0.9V
Std SIL	0.7V
LWD SIL	0.7V



Similar performance on another device



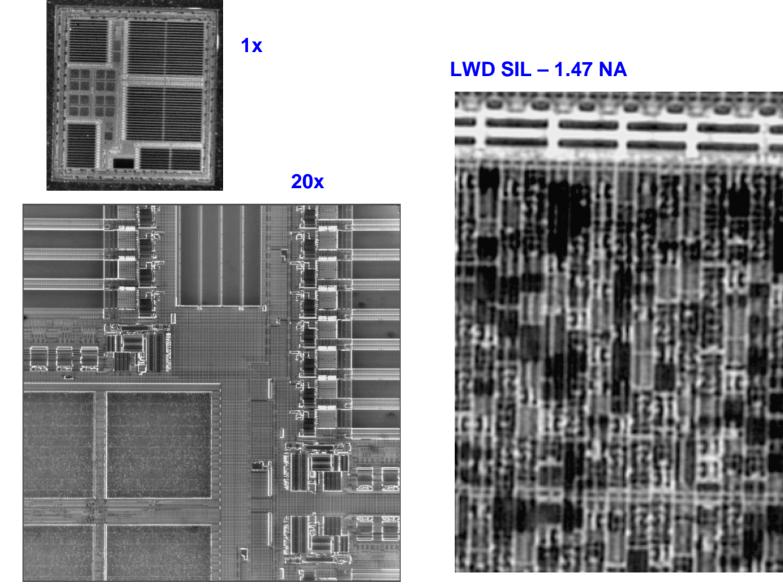
STD SIL image

Sensitivity limits

	LN2 InGaAs
1x	<0.7V
20x	0.8V
50x	0.8V
Std SIL	<0.7V

Image courtesy of ST

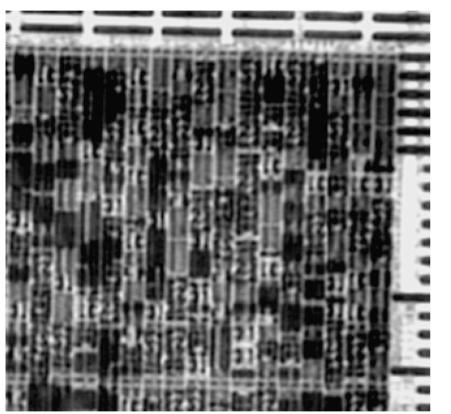
Resolution - 45nm images (1/2)



Images courtesy of ST Crolles

Resolution - 45nm images (2/2)

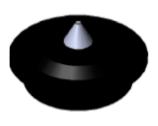
LWD SIL



STD SIL

Images courtesy of ST Crolles

1.47NA 100um Si (works from 0um to 350um)

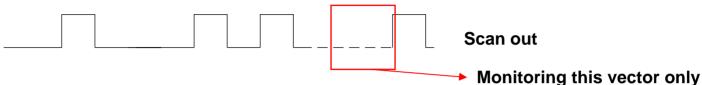


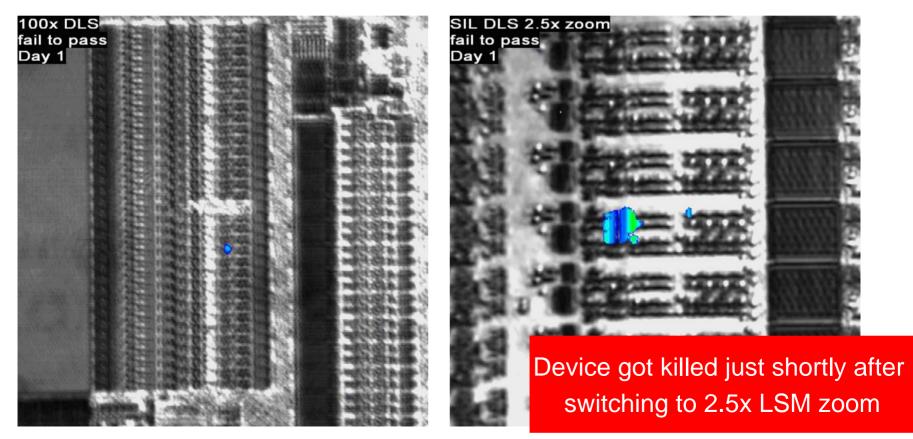


2.45NA 100um Si ± 50um

SIL for DLS applications

Customer had an issue in a memory and stated that 100x was not giving him enough resolution
The scan chain output pattern was monitored at a specific vector to determine pass or fail

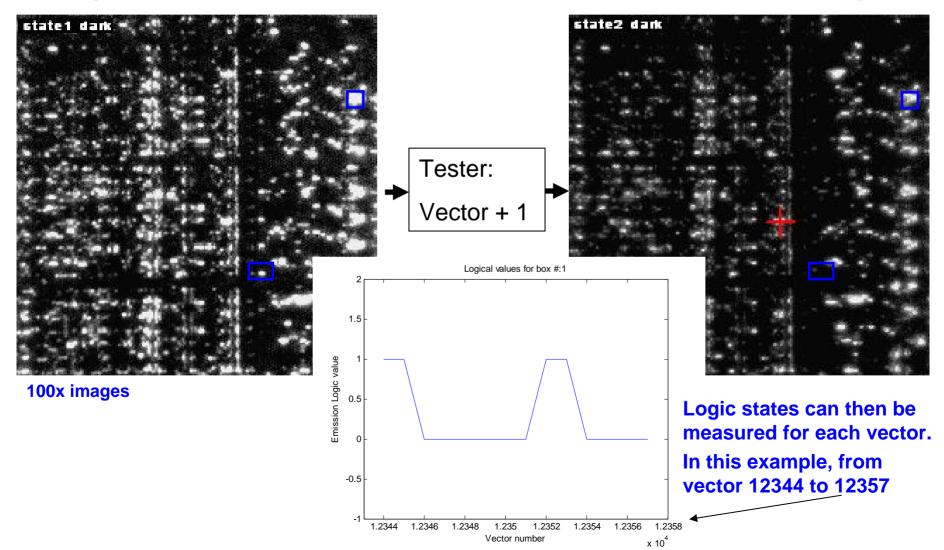




Images courtesy of Texas Instruments

SIL for Logic State Mapping

 The emission microscope is linked with the tester to take one emission image and then advance the tester to next vector and re-acquire image...



CONCLUSION

- SIL improvement for **resolution**.
 - applies for higher pixel count camera with smaller pitch
- Macro lens traditionally was the most sensitive lens
 - No longer true with SIL
 - SIL is the **most sensitive** lens
- SIL benefits both emission & LSM applications
 - Be careful not to apply too much laser power
 - Especially when using LSM optical zoom
- New SILs in development will further improve performance without comprising ease of use